

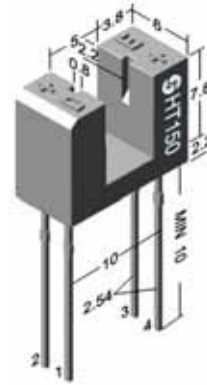
HT150

● Features

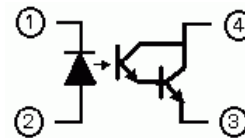
- Combines high output GaAs IRED with high sensitive photodalington transistor.
- Non-contact detecting manner.
- Slit width(resolution): 0.8mm、0.4mm、0.2mm available

● Dimensions Unit:mm

Unless otherwise specified, the tolerances are $\pm 0.2\text{mm}$



Internal Circuit



● Absolute Maximum Ratings(Ta=25°C)

Parameter		Symbol	Rating	Unit
Input	Forward Current	IF	50	mV
	Reverse Voltage	VR	6	V
	Power Dissipation	P	75	mW
Output	Collector-Emitter voltage	VCEO	25	V
	Emitter-Collector voltage	VECO	6	V
	Collector Power Dissipation	PC	50	mW
*Operating Temperature		Topr	-20~65	°C
Storage Temperature		Tstg	-30~75	°C
** Soldering Temperature		Tsol	260	°C

*The special requirement could be met according to customer's request.

**Soldering time: 5s max. soldering position: at least 1.5mm from the base of the package.

● Electro-Optical Characteristics (Ta=25°C)

Parameter		Symbol	Test Condition	Min.	Typ.	Max.	Unit	
Input	Forward Voltage	VF	IF=20mA	-	1.25	1.5	V	
	Reverse Current	IR	VR=3V	-	-	10	μA	
Output	Collector Dark Current	ICEO	VCE=20V	-	-	1	μA	
	Collector Light Current	IL	VCE=5V IF=8mA	0.8	4	-	mA	
				0.4	2	-		
				0.2	1	-		
Collector-Emitter Saturation Voltage	VCE(SAT)	IF=8 mA Ic=4mA	-	-	0.9	V		
Transfer Characteristics	Response Time	RiseTime	Tr	IF=20mA VCE=5V RC=100 Ω	-	5	-	μS
		FallTime	Tf		-	5	-	μS